

## **Blacklined Claims**

173. The circuit of Claim 172, wherein the polymeric material comprises a hydrocarbon block and a silicon-containing block.

174. The circuit of Claim 171, wherein the texturizing layer comprises a conductive material.

175. The circuit of Claim 174, wherein the texturizing layer comprises at least two conductive metals.

176. The circuit of Claim 175, wherein the texturizing layer comprises platinum, and at least one of silver and copper.

177. A semiconductor circuit, comprising a capacitor according to Claim 169.

178. A semiconductor circuit, comprising a capacitor according to Claim 170.

179. An integrated circuit, comprising:  
an array of memory cells;  
internal circuitry; and  
at least one capacitor according to Claim 160, the capacitor formed in a container and in electrical contact with an active area within a semiconductive substrate of the memory cell array.

180. The circuit of Claim 179, wherein the texturizing layer comprises a polymeric material.

181. The circuit of Claim 180, wherein the polymeric material comprises a hydrocarbon block and a silicon-containing block.

182. The circuit of Claim 179, wherein the texturizing layer comprises a conductive material.

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183. The circuit of Claim 182, wherein the texturizing layer comprises at least two conductive metals.

184. The circuit of Claim 183, wherein the texturizing layer comprises platinum, and at least one of silver and copper.

185. An integrated circuit, comprising:

an array of memory cells;

internal circuitry; and

at least one capacitor according to Claim 169, the capacitor formed in a container and in electrical contact with an active area within a semiconductive substrate of the memory cell array.

186. An integrated circuit, comprising:

an array of memory cells;

internal circuitry; and

at least one capacitor according to Claim 170, the capacitor formed in a container and in electrical contact with an active area within a semiconductive substrate of the memory cell array.

187. An integrated circuit supported by a substrate, and comprising a capacitor according to Claim 66.

188. An integrated circuit supported by a substrate, and comprising a capacitor according to Claim 130.

189. An integrated circuit supported by a substrate, and comprising a capacitor according to Claim 160.